MOSFET – Power, Single, N-Channel 30 V, 4.1 mΩ, 90 A

Features

- Low R_{DS(on)} to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	30	V
Gate-to-Source Voltage			V _{GS}	±20	V
Continuous Drain		T _C = 25°C	I _D	90	Α
Current R _{θJC} (Notes 1 & 3)	Steady	T _C = 100°C		64	
Power Dissipation R ₀ JC	State	T _C = 25°C	P _D	57	W
(Note 1)		T _C = 100°C		28	
Continuous Drain		T _A = 25°C	I _D	22	Α
Current $R_{\theta JA}$ (Notes 1, 2 & 3)	Steady	T _A = 100°C		16	
Power Dissipation R _{0JA}	State	T _A = 25°C	P _D	3.5	W
(Notes 1 & 2)		T _A = 100°C		1.7	
Pulsed Drain Current	T _A = 25°	C, t _p = 10 μs	I _{DM}	395	Α
Operating Junction and Storage Temperature			T _J , T _{stg}	-55 to 175	°C
Source Current (Body Diode)			I _S	75	Α
Single Pulse Drain-to-Source Avalanche Energy (T _J = 25°C, I _{L(pk)} = 6.9 A)			E _{AS}	133	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			TL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain) (Note 1)	$R_{\theta JC}$	2.65	°C/W
Junction-to-Ambient - Steady State (Note 2)	$R_{\theta JA}$	43	

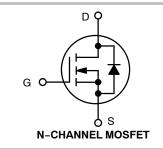
- The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
- 2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
- Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



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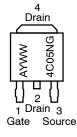
V _{(BR)DSS}	R _{DS(on)}	I _D
30 V	4.1 mΩ @ 10 V	90 A
	6.0 mΩ @ 4.5 V	90 K





DPAK CASE 369C STYLE 2

MARKING DIAGRAM & PIN ASSIGNMENT



A = Assembly Location

Y = Year

WW = Work Week

4C05N = Device Code

G = Pb-Free Package

ORDERING INFORMATION

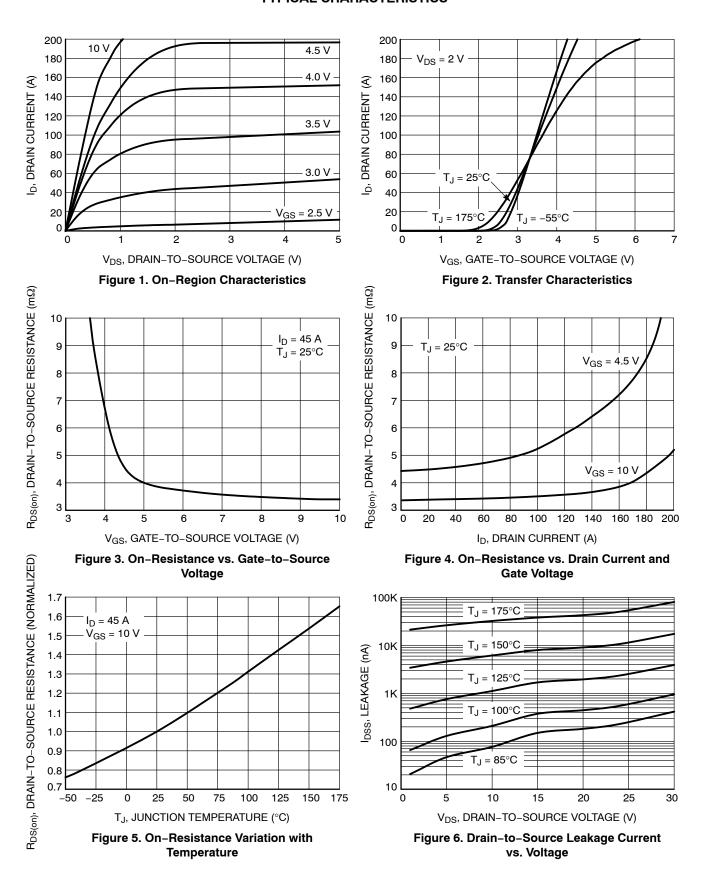
See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS ($T_J = 25$ °C unless otherwise noted)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS	<u> </u>						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA		30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J				14.9		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	Voc = 0 V	T _J = 25°C			1.0	μΑ
		$V_{GS} = 0 V$, $V_{DS} = 24 V$	T _J = 125°C			10	
Gate-to-Source Leakage Current	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS}$	= ±20 V			±100	nA
ON CHARACTERISTICS (Note 4)	•		•		•	-	
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_D =$	= 250 μA	1.3		2.2	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J				4.7		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D	= 45 A		3.4	4.1	mΩ
		V _{GS} = 4.5 V, I _D = 45 A			4.5	6.0	
Forward Transconductance	g _{FS}	V _{DS} = 2 V, I _D	= 45 A		98		S
CHARGES, CAPACITANCES AND GATE RE	SISTANCES		•		•		
Input Capacitance	C _{iss}	$V_{GS} = 0 \text{ V, f} = 1.0 \text{ MHz,}$ $V_{DS} = 25 \text{ V}$			1970		pF
Output Capacitance	C _{oss}				725		
Reverse Transfer Capacitance	C _{rss}				30		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 24 V, I _D = 45 A			31		nC
Total Gate Charge	Q _{G(TOT)}				14		nC
Threshold Gate Charge	Q _{G(TH)}				3.3		1
Gate-to-Source Charge	Q _{GS}	$V_{GS} = 4.5 \text{ V}, V_{D}$ $I_{D} = 45 \text{ A}$	S = 24 V,		6.2		
Gate-to-Drain Charge	Q _{GD}	10 - 40 /	`		3.2		
Plateau Voltage	V _{GP}	1			3.1		V
Gate Resistance	R_{G}				1.0		Ω
SWITCHING CHARACTERISTICS (Note 5)			•		•		
Turn-On Delay Time	t _{d(on)}				11		ns
Rise Time	t _r	V _{GS} = 4.5 V, V _D	s = 24 V.		107		
Turn-Off Delay Time	t _{d(off)}	$V_{GS} = 4.3 \text{ V}, V_{DS} = 24 \text{ V},$ $I_{D} = 45 \text{ A}, R_{G} = 0 \Omega$			17		
Fall Time	t _f				6.0		
DRAIN-SOURCE DIODE CHARACTERISTIC	S				-		_
Forward Diode Voltage	V_{SD}	$V_{GS} = 0 \text{ V},$ $I_{S} = 45 \text{ A}$ $T_{J} = 25^{\circ}\text{C}$ $T_{J} = 125^{\circ}\text{C}$	$T_J = 25^{\circ}C$		0.9	1.2	V
			T _J = 125°C		0.8		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dls/dt = 100 A/μs, I _S = 45 A			41		ns
Charge Time	ta				21		
Discharge Time	tb				20		
Reverse Recovery Charge	Q _{RR}				26		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 4. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%. 5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS

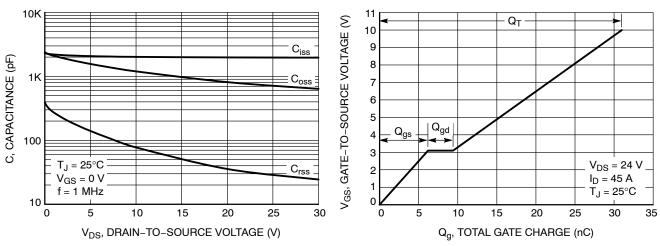


Figure 7. Capacitance Variation

Figure 8. Gate-to-Source vs. Total Charge

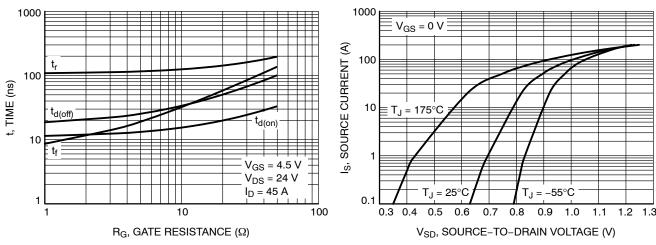


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

Figure 10. Diode Forward Voltage vs. Current

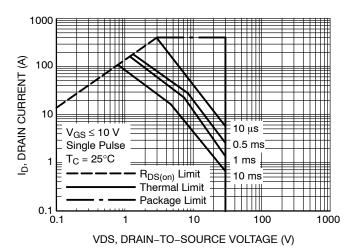


Figure 11. Maximum Rated Forward Biased Safe Operating Area

TYPICAL CHARACTERISTICS

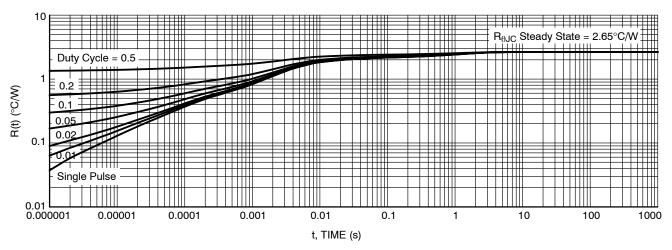


Figure 12. Thermal Impedance (Junction-to-Case)

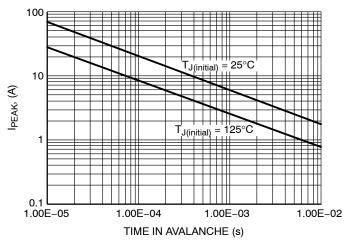


Figure 13. Avalanche Characteristics

ORDERING INFORMATION

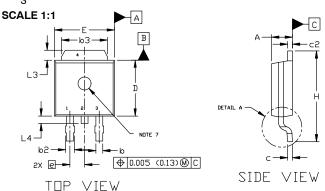
Order Number	Package	Shipping [†]
NVD4C05NT4G	DPAK (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





DATE 31 MAY 2023



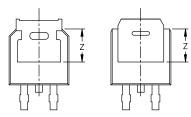


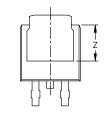
- DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994. CONTROLLING DIMENSION: INCHES
- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS 63,
- L3. AND Z. L3, AND Z.

 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
 PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR
 GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
 DIMENSIONS D AND E ARE DETERMINED AT THE
 OUTERMOST EXTREMES OF THE PLASTIC BODY.
 DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
 DETININAL MOLD ESCALUPE.

- OPTIONAL MOLD FEATURE.

DIM	DIM INCHES		MILLIM	ETERS
MIM	MIN.	MAX.	MIN.	MAX.
Α	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
C	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090	BSC	2.29 BSC	
Н	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114	0.114 REF		REF
L2	0.020 BSC		0.51	BSC
L3	0.035	0.050	0.89	1.27
L4		0.040		1.01
Z	0.155		3.93	

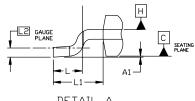




BOTTOM VIEW

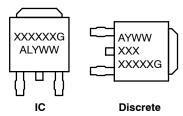
BOTTOM VIEW ALTERNATE CONSTRUCTIONS

5.80 [0.228] 6.20 [0.244] 2.58 3.00 [0.102] [0.118] 1.60 [0.063] 6.17 [0.243]



DETAIL A ROTATED 90° CW

GENERIC MARKING DIAGRAM*



XXXXXX	= Device Code
Α	= Assembly Location
L	= Wafer Lot
Υ	= Year
WW	= Work Week
G	= Pb-Free Package

*This information is generic. Please refer to

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DUWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

3 FMITTER

4. COLLECTOR

s

3 GATE

RECOMMENDED MOUNTING FOOTPRINT*

STYLE 1: STYLE 2: PIN 1. BASE PIN 1. GATE 2. COLLECTOR 2. DRAIL 3. EMITTER 3. SOUF 4. COLLECTOR 4. DRAIL	N 2. CATHODE RCE 3. ANODE	3. GATE	STYLE 5: PIN 1. GATE 2. ANODE 3. CATHODE 4. ANODE
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STYLE 7: PIN 1. GATE 2. COLLECTOR STYLE 6: STYLE 8: STYLE 9: STYLE 10: PIN 1. MT1 2. MT2 PIN 1. N/C 2. CATHODE 3. ANODE PIN 1. ANODE 2. CATHODE

4. CATHODE

device data sheet for actual part marking. PIN 1. CATHODE 2. ANODE 3. CATHODE Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may 3 RESISTOR ADJUST not follow the Generic Marking. 4. ANODE

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DESCRIPTION:	DPAK (SINGLE GAUGE)		PAGE 1 OF 1

4. CATHODE

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